

International Rectifier

RADIATION HARDENED POWER MOSFET SURFACE-MOUNT (SMD-2)

PD - 94342

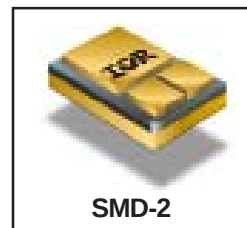
IRHNA67260 200V, N-CHANNEL TECHNOLOGY

Product Summary

Part Number	Radiation Level	RDS(on)	Id
IRHNA67260	100K Rads (Si)	0.028Ω	63A
IRHNA63260	300K Rads (Si)	0.028Ω	63A
IRHNA64260	600K Rads (Si)	0.028Ω	63A
IRHNA68260	1000K Rads (Si)	0.028Ω	63A

International Rectifier's R6™ technology provides superior power MOSFETs for space applications. These devices have improved immunity to Single Event Effect (SEE) and have been characterized for useful performance with Linear Energy Transfer (LET) up to 90MeV/(mg/cm²).

Their combination of very low RDS(on) and faster switching times reduces power loss and increases power density in today's high speed switching applications such as DC-DC converters and motor controllers. These devices retain all of the well established advantages of MOSFETs such as voltage control, ease of paralleling and temperature stability of electrical parameters.



SMD-2

Features:

- Low RDS(on)
- Fast Switching
- Single Event Effect (SEE) Hardened
- Low Total Gate Charge
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Ceramic Package
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
Id @ VGS = 12V, TC = 25°C	Continuous Drain Current	63	A
Id @ VGS = 12V, TC = 100°C	Continuous Drain Current	40	
IDM	Pulsed Drain Current ①	252	
Pd @ TC = 25°C	Max. Power Dissipation	250	W
	Linear Derating Factor	2.0	W/°C
VGS	Gate-to-Source Voltage	±20	V
EAS	Single Pulse Avalanche Energy ②	246	mJ
IAR	Avalanche Current ①	63	A
EAR	Repetitive Avalanche Energy ①	25	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
TJ	Operating Junction	-55 to 150	°C
TSTG	Storage Temperature Range		
	Pckg. Mounting Surface Temp.	300 (for 5s)	
	Weight	3.3 (Typical)	g

For footnotes refer to the last page

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1

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Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	—	V	V _{GS} = 0V, I _D = 1.0mA
ΔBV _{DSS} /ΔT _J	Temperature Coefficient of Breakdown Voltage	—	0.17	—	V/°C	Reference to 25°C, I _D = 1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.028	Ω	V _{GS} = 12V, I _D = 40A ④
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} = V _{GS} , I _D = 1.0mA
g _{fs}	Forward Transconductance	40	—	—	S (⑦)	V _{DS} = 25V, I _{DS} = 40A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	10	μA	V _{DS} = 160V, V _{GS} = 0V
		—	—	25		V _{DS} = 160V, V _{GS} = 0V, T _J = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V _{GS} = -20V
Q _g	Total Gate Charge	—	—	240	nC	V _{GS} = 12V, I _D = 63A V _{DS} = 100V
Q _{gs}	Gate-to-Source Charge	—	—	70		
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	60		
t _{d(on)}	Turn-On Delay Time	—	—	40	ns	V _{DD} = 100V, I _D = 63A, V _{GS} = 12V, R _G = 2.35Ω
t _r	Rise Time	—	—	60		
t _{d(off)}	Turn-Off Delay Time	—	—	70		
t _f	Fall Time	—	—	30		
L _S + L _D	Total Inductance	—	2.8	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	8100	—	pF	V _{GS} = 0V, V _{DS} = 25V f = 1.0MHz
C _{oss}	Output Capacitance	—	955	—		
C _{rss}	Reverse Transfer Capacitance	—	1.6	—		
R _g	Internal Gate Resistance	—	1.1	—	Ω	f = 0.73MHz, open drain

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	63	A	T _J = 25°C, I _S = 63A, V _{GS} = 0V ④
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	252		
V _{SD}	Diode Forward Voltage	—	—	1.2	V	T _J = 25°C, I _F = 63A, di/dt ≤ 100A/μs V _{DD} ≤ 25V ④
t _{rr}	Reverse Recovery Time	—	—	640	ns	
Q _{RR}	Reverse Recovery Charge	—	—	11.7	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	0.5	°C/W	

Note: Corresponding Spice and Saber models are available on International Rectifier Web site.

For footnotes refer to the last page

Radiation Characteristics

IRHNA67260

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	Up to 600K Rads(Si) ¹		1000K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	200	—	200	—	V	V _{GS} = 0V, I _D = 1.0mA
V _{GS(th)}	Gate Threshold Voltage	2.0	4.0	1.5	4.0		V _{GS} = V _{DS} , I _D = 1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V _{GS} = 20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V _{GS} = -20V
I _{DSS}	Zero Gate Voltage Drain Current	—	10	—	25	μA	V _{DS} = 160V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.029	—	0.029	Ω	V _{GS} = 12V, I _D = 40A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (SMD-2)	—	0.028	—	0.028	Ω	V _{GS} = 12V, I _D = 40A
V _{SD}	Diode Forward Voltage ④	—	1.2	—	1.2	V	V _{GS} = 0V, I _S = 63A

1. Part numbers IRHNA67260, IRHNA63260 and IRHNA64260

2. Part number IRHNA68260

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	VDS (V)							
				@VGS= 0V	@VGS= -5V	@VGS= -10V	@VGS= -15V	@VGS= -17V	@VGS= -18V	@VGS= -19V	@VGS= -20V
Xe	59	825	66	200	200	200	200	170	160	-	-
Xe	43	2441	205	200	200	200	200	200	190	180	150

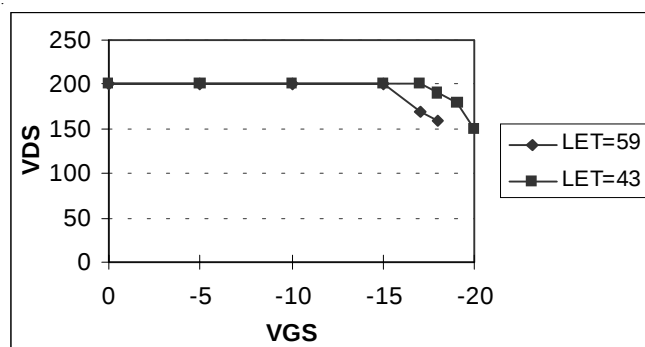


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

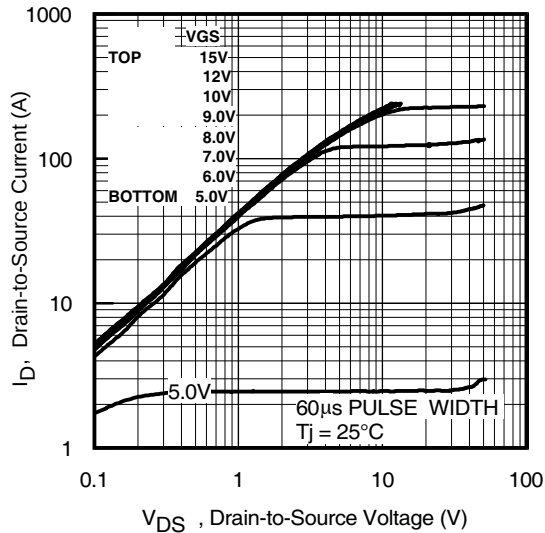


Fig 1. Typical Output Characteristics

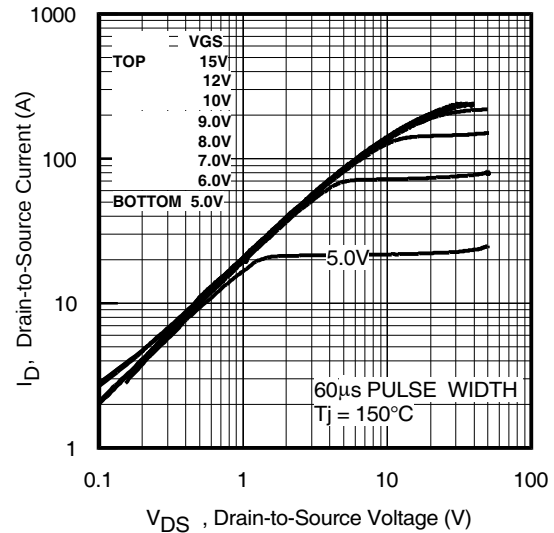


Fig 2. Typical Output Characteristics

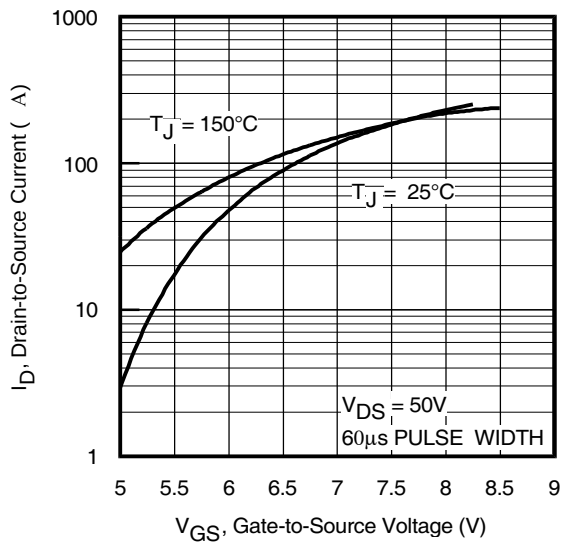
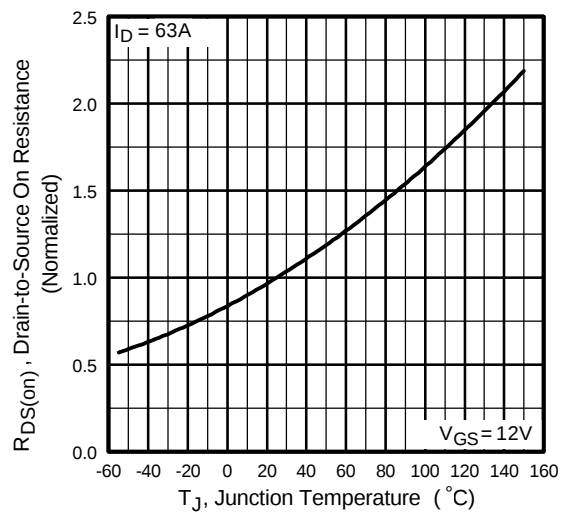


Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance
Vs. Temperature

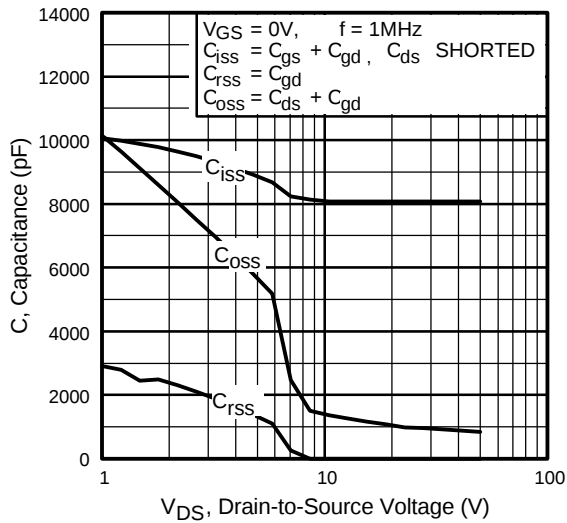


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

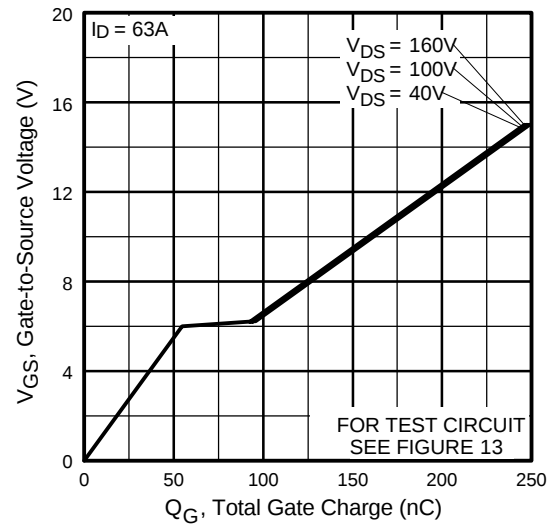


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

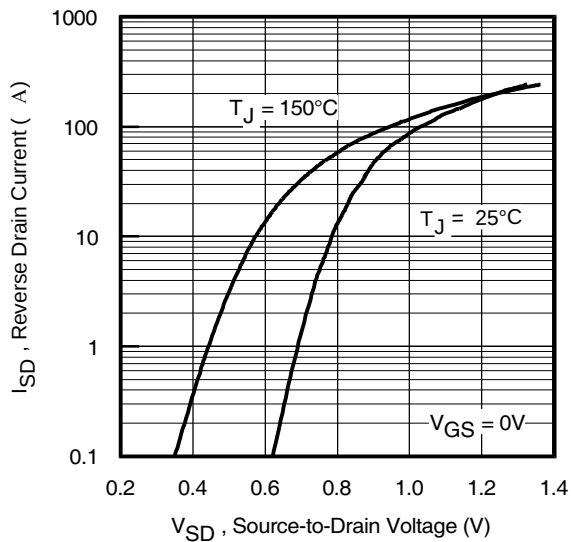


Fig 7. Typical Source-Drain Diode Forward Voltage

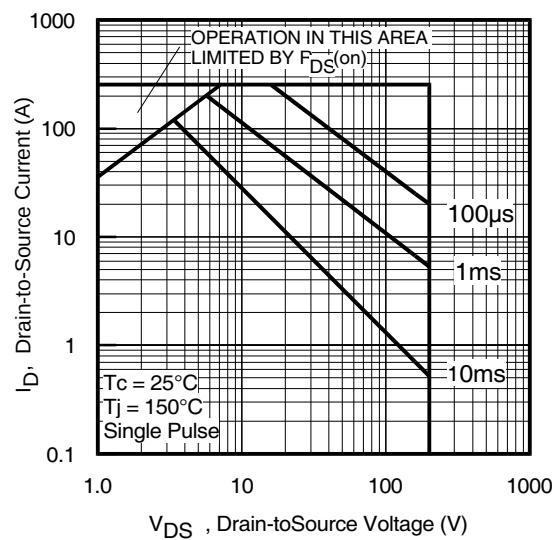


Fig 8. Maximum Safe Operating Area

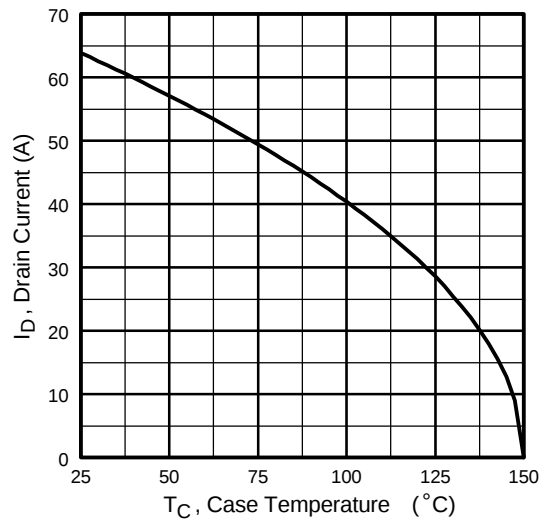


Fig 9. Maximum Drain Current Vs. Case Temperature

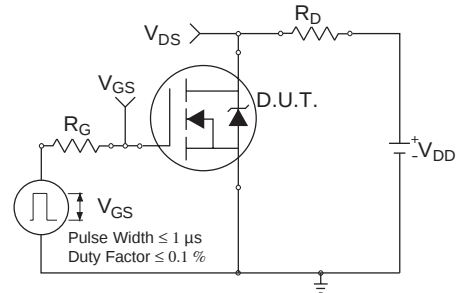


Fig 10a. Switching Time Test Circuit

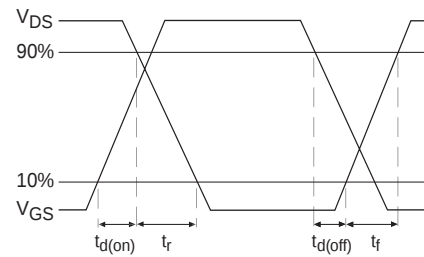


Fig 10b. Switching Time Waveforms

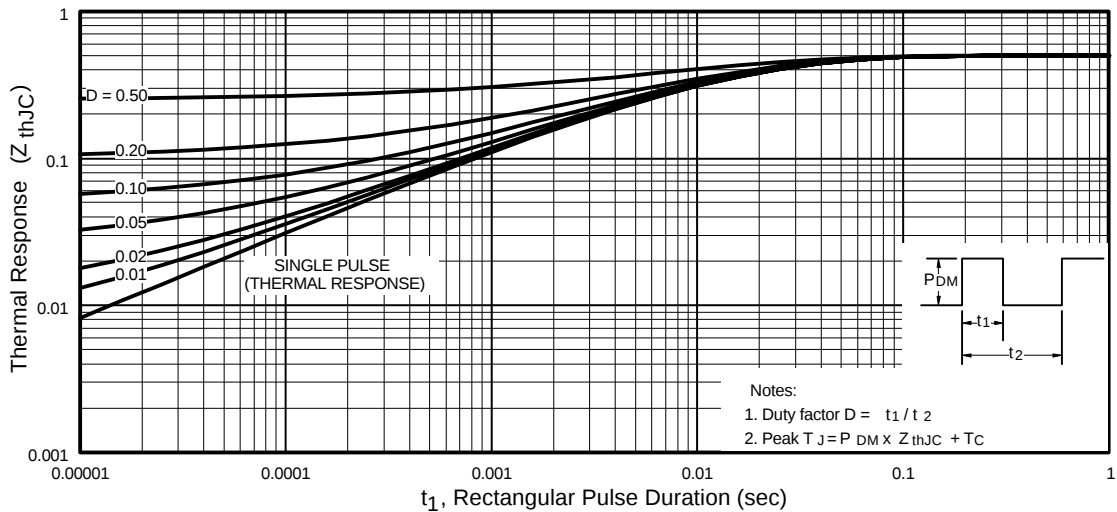


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

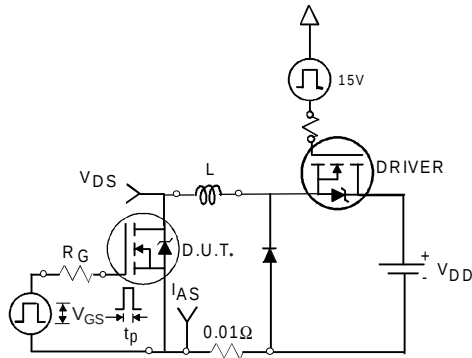


Fig 12a. Unclamped Inductive Test Circuit

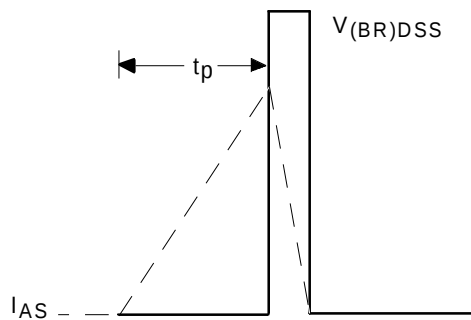


Fig 12b. Unclamped Inductive Waveforms

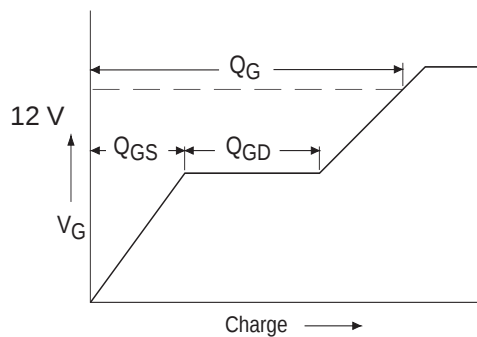


Fig 13a. Basic Gate Charge Waveform

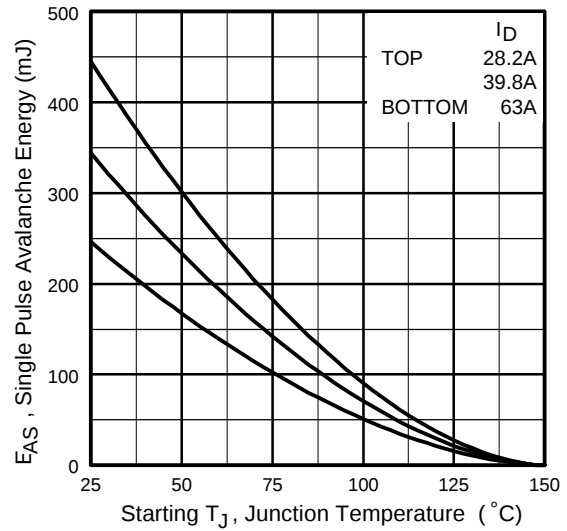


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

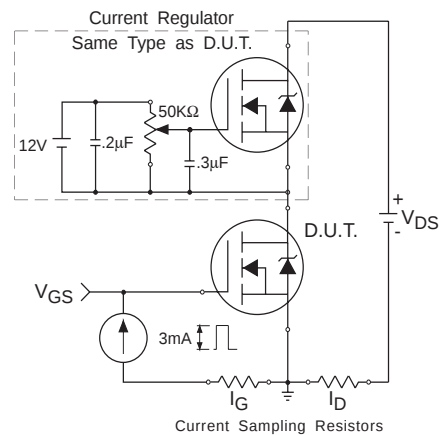
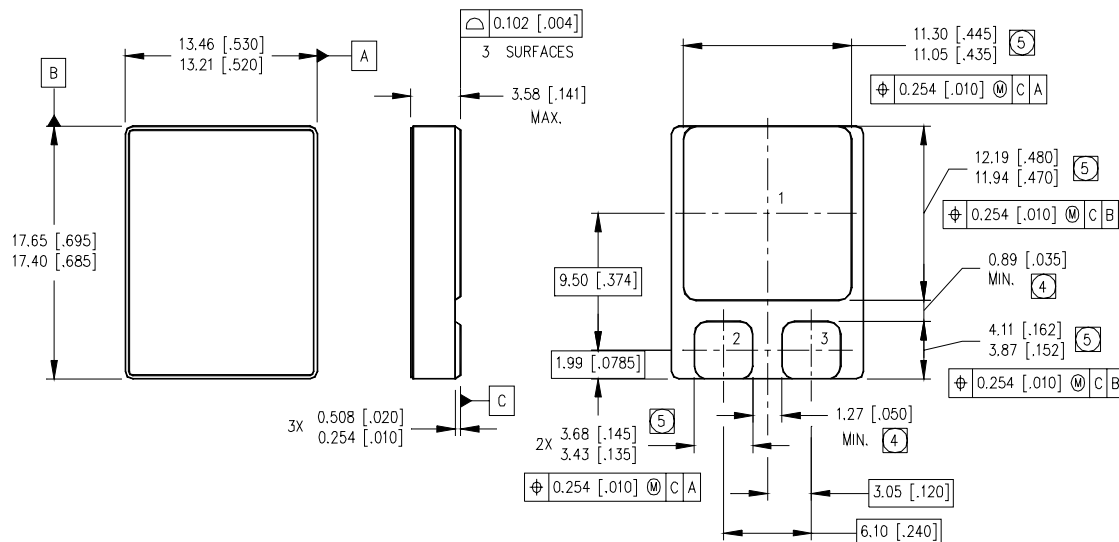


Fig 13b. Gate Charge Test Circuit

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ C$, $L = 0.124\text{ mH}$
Peak $I_L = 63A$, $V_{GS} = 12V$
- ③ $ISD \leq 63A$, $di/dt \leq 875A/\mu s$,
 $V_{DD} \leq 200V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300\text{ }\mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
160 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — SMD-2**NOTES:**

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- ④ DIMENSION INCLUDES METALLIZATION FLASH.
- ⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

- | | | |
|---|---|--------|
| 1 | = | DRAIN |
| 2 | = | GATE |
| 3 | = | SOURCE |

International
IR Rectifier

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